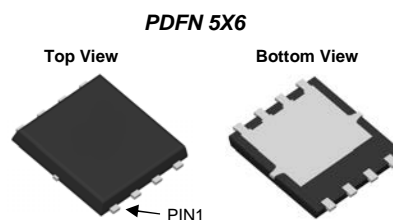


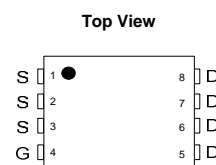
Product Summary

- 40V, 240A
 $R_{DS(ON)} = 1.0\text{m}\Omega @ V_{GS} = 10\text{V (Typ.)}$



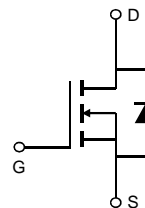
Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Halogen-free; RoHS-compliant
- Pb-free plating



Applications

- Load Switch
- PWM Application
- Power Management



Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|---|---------------------------|------------|------------------|
| Drain-to-Source Voltage | V_{DS} | 40 | V |
| Gate-to-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current ⁽¹⁾ | $T_C = 25^\circ\text{C}$ | 240 | A |
| | $T_C = 100^\circ\text{C}$ | 151 | |
| Pulsed Drain Current ⁽²⁾ | I_{DM} | 960 | A |
| Avalanche Energy ⁽³⁾ | E_{AS} | 600 | mJ |
| Power Dissipation ⁽⁴⁾ | $T_C = 25^\circ\text{C}$ | 138 | W |
| | $T_C = 100^\circ\text{C}$ | 55 | |
| Junction & Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ |



Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|---|---------------|--|------|------|------------|------------------|
| STATIC PARAMETERS | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$ | 40 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 32\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$ | | | 1.0 5.0 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$ | | | ± 100 | nA |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$ | 1.0 | 1.5 | 2.5 | V |
| Static Drain-Source ON-Resistance | $R_{DS(ON)}$ | $V_{GS} = 10\text{V}$, $I_D = 20\text{A}$ | | 1.0 | 1.4 | $\text{m}\Omega$ |
| Forward Transconductance | g_{FS} | $V_{DS} = 5\text{V}$, $I_D = 20\text{A}$ | | 62 | | S |
| Diode Forward Voltage | V_{SD} | $I_S = 1\text{A}$, $V_{GS} = 0\text{V}$ | | 0.70 | 1.0 | V |
| Diode Continuous Current | I_S | $T_C = 25^\circ\text{C}$ | | | 138 | A |
| DYNAMIC PARAMETERS ⁽⁵⁾ | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 20\text{V}$, $f = 1\text{MHz}$ | | 8628 | | pF |
| Output Capacitance | C_{oss} | | | 1279 | | pF |
| Reverse Transfer Capacitance | C_{rss} | | | 1241 | | pF |
| Gate Resistance | R_g | $V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$ | | 0.5 | | Ω |
| SWITCHING PARAMETERS ⁽⁵⁾ | | | | | | |
| Total Gate Charge (@ $V_{GS} = 10\text{V}$) | Q_g | $V_{GS} = 0$ to 10V $V_{DS} = 20\text{V}$, $I_D = 20\text{A}$ | | 71 | | nC |
| Total Gate Charge (@ $V_{GS} = 6.0\text{V}$) | Q_g | | | 43 | | nC |
| Gate Source Charge | Q_{gs} | | | 22 | | nC |
| Gate Drain Charge | Q_{gd} | | | 11.7 | | nC |
| Turn-On DelayTime | $t_{D(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 20\text{V}$ $R_L = 1.0\Omega$, $R_{GEN} = 6\Omega$ | | 20 | | ns |
| Turn-On Rise Time | t_r | | | 37 | | ns |
| Turn-Off DelayTime | $t_{D(off)}$ | | | 60 | | ns |
| Turn-Off Fall Time | t_f | | | 28 | | ns |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = 20\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$ | | 75 | | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | $I_F = 20\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$ | | 67 | | nC |

Thermal Performance

| Parameter | Symbol | Typ. | Max. | Unit |
|---|-----------------|------|------|---------------------------|
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 45 | 52 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 0.90 | 1.1 | $^\circ\text{C}/\text{W}$ |

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. E_{AS} of 600mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 3.0\text{mH}$, $I_{AS} = 20\text{A}$, $V_{GS} = 10\text{V}$, $V_{DD} = 20\text{V}$; 100% test at $L = 0.5\text{mH}$, $I_{AS} = 42\text{A}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

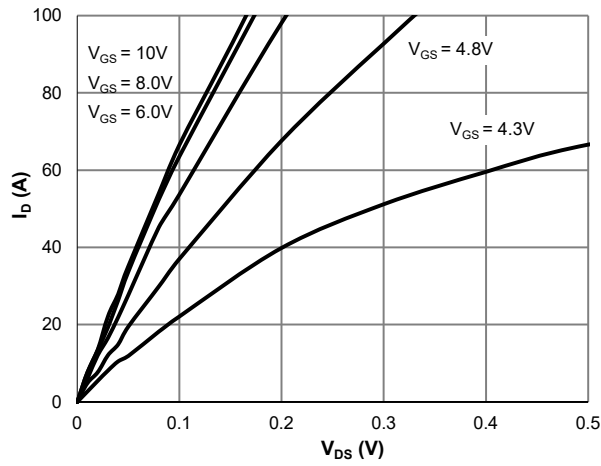


Figure 1: Saturation Characteristics

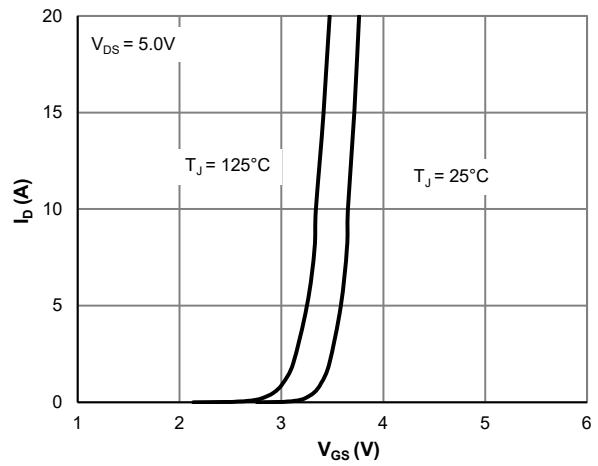


Figure 2: Transfer Characteristics

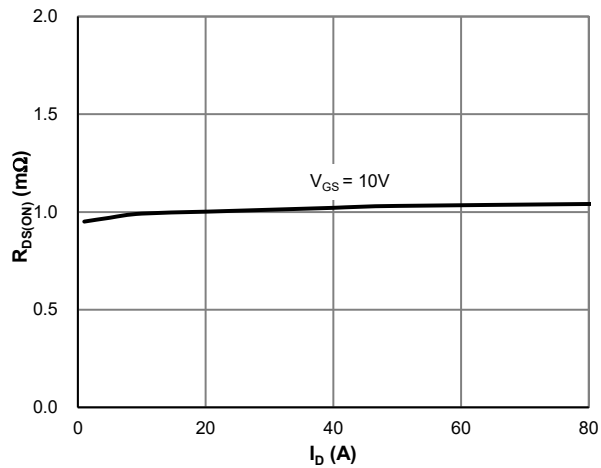


Figure 3: $R_{DS(ON)}$ vs. Drain Current

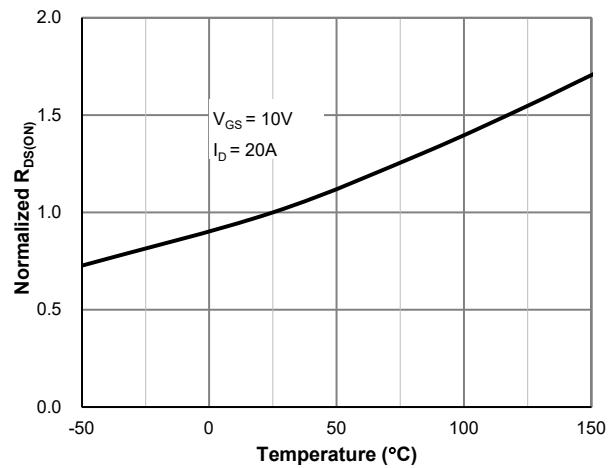


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

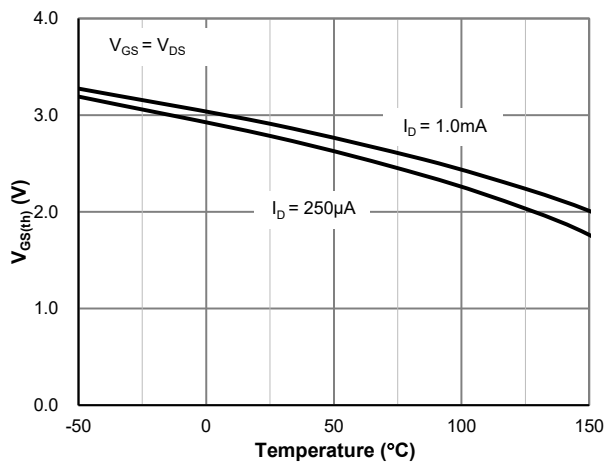


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

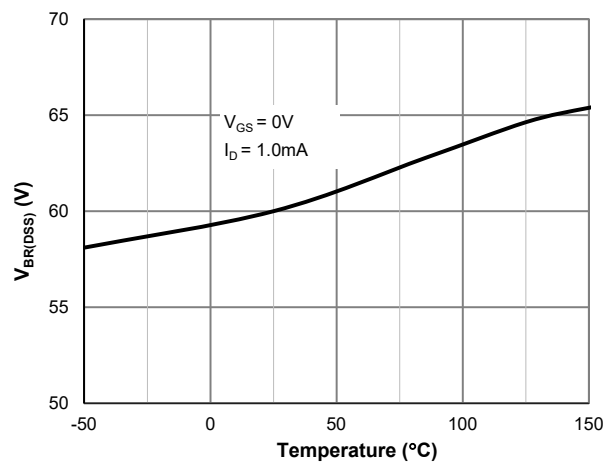


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

Typical Electrical & Thermal Characteristics

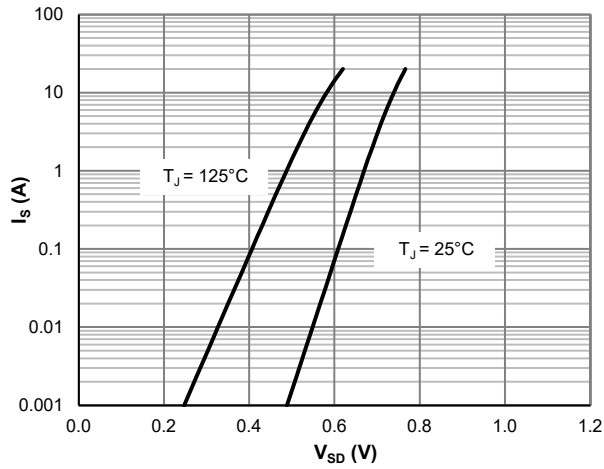


Figure 7: Body-Diode Characteristics

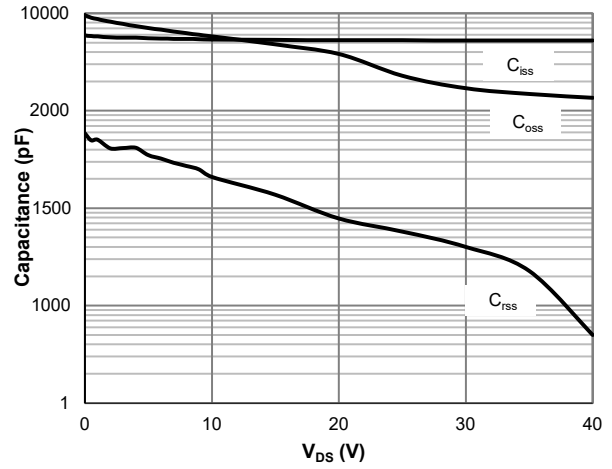


Figure 8: Capacitance Characteristics

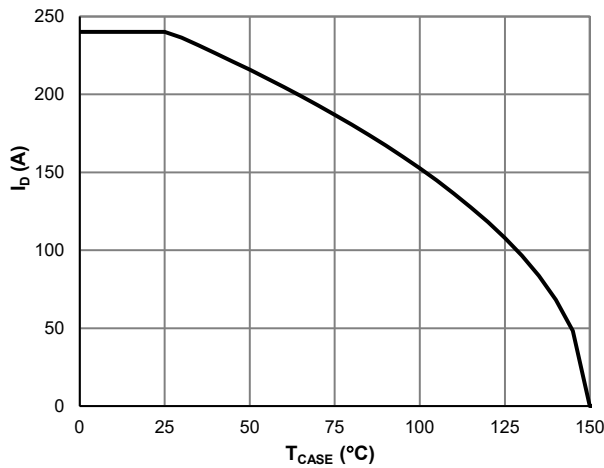


Figure 9: Current De-rating

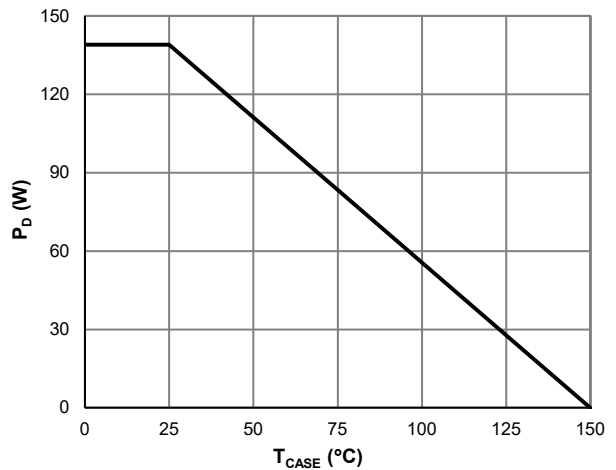


Figure 10: Power De-rating

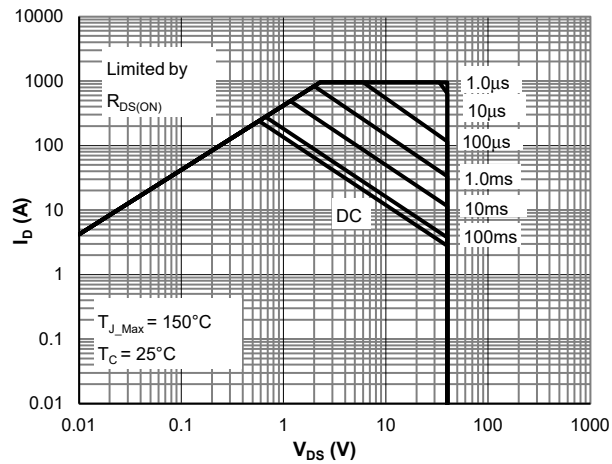


Figure 11: Maximum Safe Operating Area

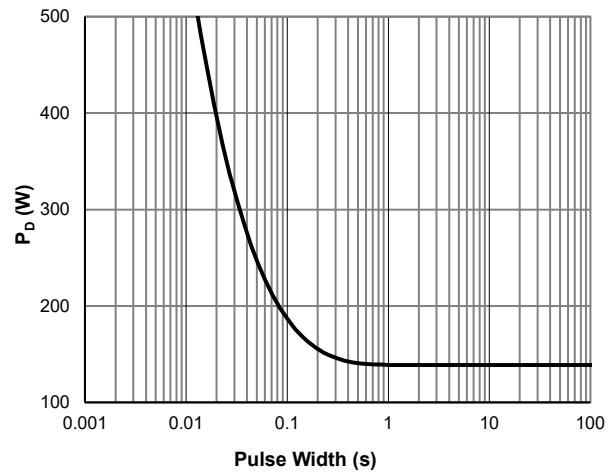


Figure 12: Single Pulse Power Rating, Junction-to-Case

Typical Electrical & Thermal Characteristics

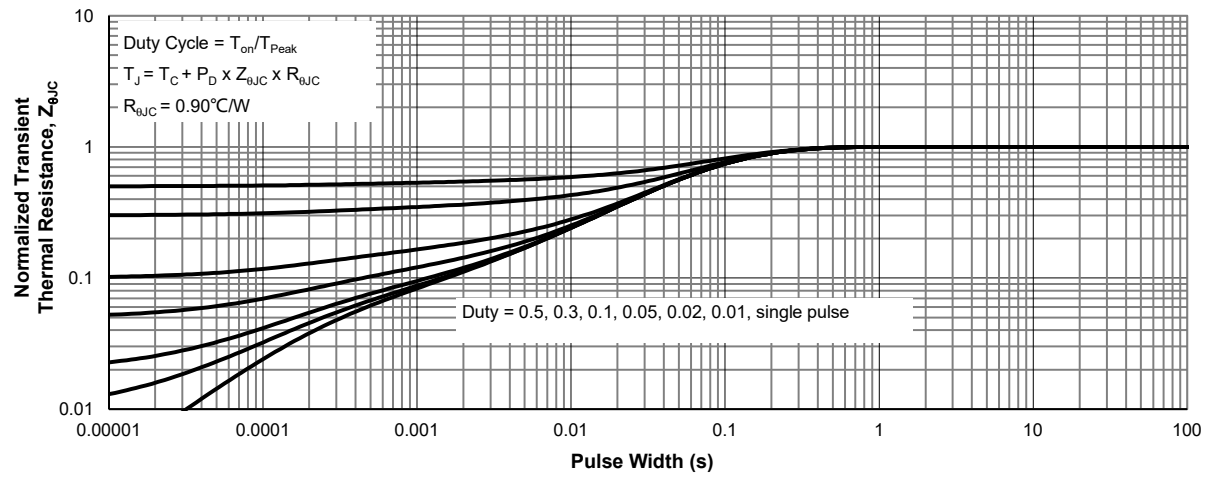
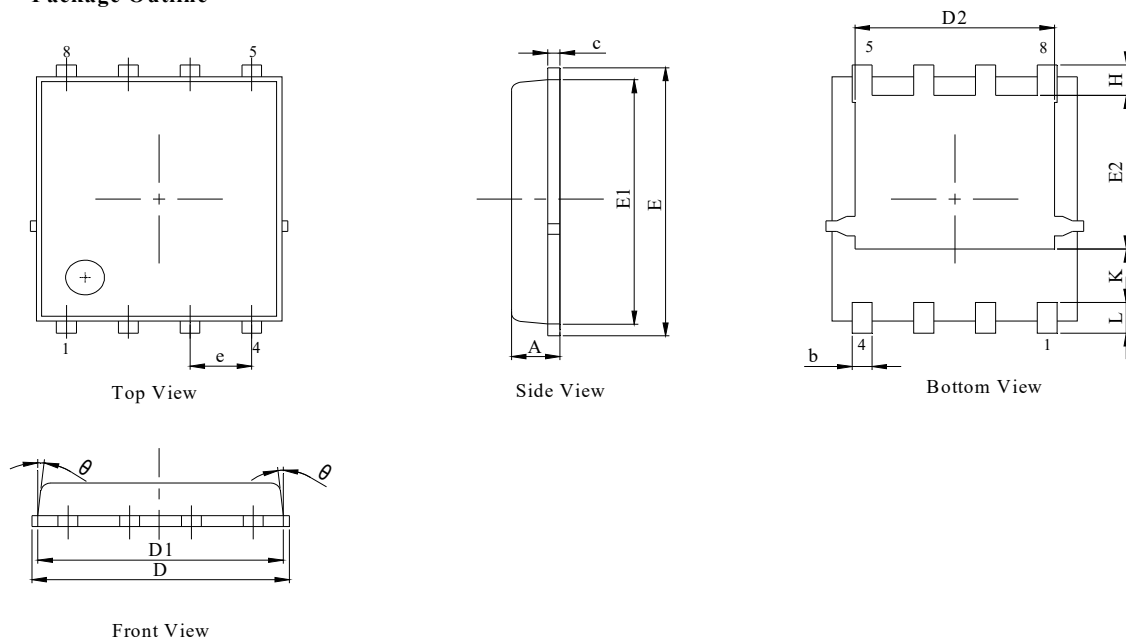


Figure 13: Normalized Maximum Transient Thermal Impedance

PDFN5x6-8L Package Information

Package Outline

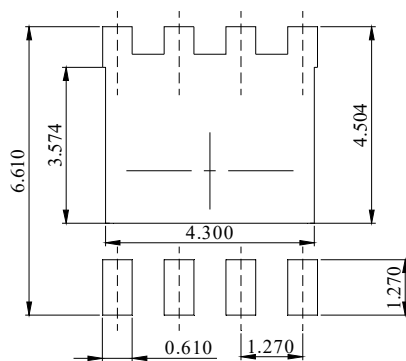


NOTES:

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter (angle in degree).
3. Dimensions D1 and E1 do not include mold flash protrusions or gate burrs.

| DIM. | MILLIMETER | | |
|------|------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.90 | 1.00 | 1.10 |
| b | 0.31 | 0.41 | 0.51 |
| c | 0.20 | 0.25 | 0.30 |
| D | 5.00 | 5.20 | 5.40 |
| D1 | 4.95 | 5.05 | 5.15 |
| D2 | 4.00 | 4.10 | 4.20 |
| E | 6.05 | 6.15 | 6.25 |
| E1 | 5.50 | 5.60 | 5.70 |
| E2 | 3.42 | 3.53 | 3.63 |
| e | 1.27BSC | | |
| H | 0.60 | 0.70 | 0.80 |
| L | 0.50 | 0.70 | 0.80 |
| K | 1.23 REF | | |
| θ | - | - | 10° |

Recommended Soldering Footprint



DIMENSIONS:MILLIMETERS